

VS4518AS-VB Datasheet

P-Channel 40 V (D-S) MOSFET

PRODUCT SUMMARY

V_{DS} (V)	$R_{DS(on)}$ (Ω) Max.	I_D (A)	Q_g (Typ.)
- 40	0.0176 at $V_{GS} = -10$ V	- 8 ^d	35.4 nC
	0.0208 at $V_{GS} = -4.5$ V	- 7 ^d	

FEATURES

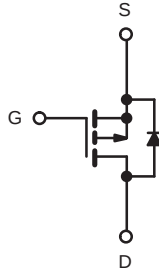
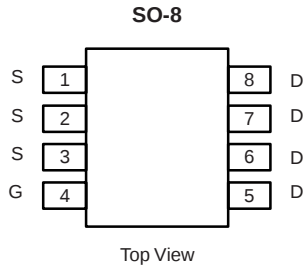
- 100% R_g and UIS Tested



RoHS
COMPLIANT
HALOGEN
FREE

APPLICATIONS

- Adaptor Switch
- Load Switch
- Power Management
- Mobile Computing



P-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS ($T_A = 25^\circ\text{C}$, unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V_{DS}	- 40	V
Gate-Source Voltage	V_{GS}	± 20	
Continuous Drain Current ($T_J = 150^\circ\text{C}$)	I_D	$T_C = 25^\circ\text{C}$ - 8 ^d	A
		$T_C = 70^\circ\text{C}$ - 7 ^d	
		$T_A = 25^\circ\text{C}$ - 7.7 ^{a, b}	
		$T_A = 70^\circ\text{C}$ - 7.7 ^{a, b}	
Pulsed Drain Current ($t = 300 \mu\text{s}$)	I_{DM}	- 32	
Continuous Source-Drain Diode Current	I_S	$T_C = 25^\circ\text{C}$ - 18 ^d	
		$T_A = 25^\circ\text{C}$ - 3 ^{a, b}	
Avalanche Current	I_{AS}	- 20	
Single-Pulse Avalanche Energy	E_{AS}	20	mJ
Maximum Power Dissipation	P_D	$T_C = 25^\circ\text{C}$ 52	W
		$T_C = 70^\circ\text{C}$ 33	
		$T_A = 25^\circ\text{C}$ 3.7 ^{a, b}	
		$T_A = 70^\circ\text{C}$ 2.4 ^{a, b}	
Operating Junction and Storage Temperature Range	T_J, T_{stg}	- 55 to 150	$^\circ\text{C}$
Soldering Recommendations (Peak Temperature) ^{e, f}		260	

THERMAL RESISTANCE RATINGS

Parameter	Symbol	Typical	Maximum	Unit
Maximum Junction-to-Ambient ^{a, c}	R_{thJA}	26	33	$^\circ\text{C/W}$
Maximum Junction-to-Case	R_{thJC}	1.9	2.4	

Notes:

- Surface mounted on 1" x 1" FR4 board.
- $t = 10$ s.
- Maximum under steady state conditions is 81 $^\circ\text{C/W}$.
- Package limited.

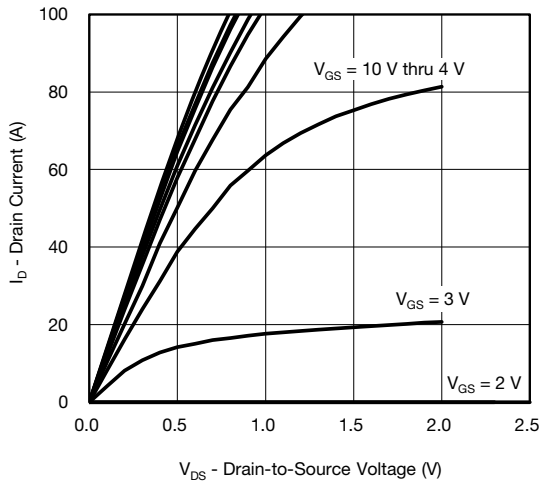
SPECIFICATIONS (T _J = 25 °C, unless otherwise noted)						
Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
Static						
Drain-Source Breakdown Voltage	V _{DS}	V _{GS} = 0 V, I _D = - 250 μA	- 40			V
V _{DS} Temperature Coefficient	ΔV _{DS} /T _J	I _D = - 250 μA		- 23		mV/°C
V _{GS(th)} Temperature Coefficient	ΔV _{GS(th)} /T _J			4.6		
Gate-Source Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = - 250 μA	- 1		- 2.5	V
Gate-Source Leakage	I _{GSS}	V _{DS} = 0 V, V _{GS} = ± 20 V			± 100	nA
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = - 40 V, V _{GS} = 0 V			- 1	μA
		V _{DS} = - 40 V, V _{GS} = 0 V, T _J = 55 °C			- 5	
On-State Drain Current ^a	I _{D(on)}	V _{DS} ≥ - 10 V, V _{GS} = - 10 V	- 30			A
Drain-Source On-State Resistance ^a	R _{DS(on)}	V _{GS} = - 10 V, I _D = - 15 A		0.0176		Ω
		V _{GS} = - 4.5 V, I _D = - 10 A		0.0208		
Forward Transconductance ^a	g _{fs}	V _{DS} = - 10 V, I _D = - 15 A		50		S
Dynamic ^b						
Input Capacitance	C _{iss}	V _{DS} = - 15 V, V _{GS} = 0 V, f = 1 MHz		3280		pF
Output Capacitance	C _{oss}			427		
Reverse Transfer Capacitance	C _{rss}			382		
Total Gate Charge	Q _g	V _{DS} = - 15 V, V _{GS} = - 10 V, I _D = - 10 A		73	110	nC
		V _{DS} = - 15 V, V _{GS} = - 4.5 V, I _D = - 10 A		35.4	53	
Gate-Source Charge	Q _{gs}			10.6		
Gate-Drain Charge	Q _{gd}			11.6		
Gate Resistance	R _g	f = 1 MHz	0.4	1.6	3.2	Ω
Turn-On Delay Time	t _{d(on)}	V _{DD} = - 15 V, R _L = 1.5 Ω I _D ≡ - 10 A, V _{GEN} = - 10 V, R _g = 1 Ω		11	22	ns
Rise Time	t _r			11	22	
Turn-Off DelayTime	t _{d(off)}			45	90	
Fall Time	t _f			8	16	
Turn-On Delay Time	t _{d(on)}	V _{DD} = - 15 V, R _L = 1.5 Ω I _D ≡ - 10 A, V _{GEN} = - 4.5 V, R _g = 1 Ω		55	100	
Rise Time	t _r			82	150	
Turn-Off DelayTime	t _{d(off)}			40	80	
Fall Time	t _f			13	26	
Drain-Source Body Diode Characteristics						
Continous Source-Drain Diode Current	I _S	T _C = 25 °C			- 18	A
Pulse Diode Forward Current	I _{SM}				- 70	
Body Diode Voltage	V _{SD}	I _S = - 3 A, V _{GS} = 0 V		- 0.74	- 1.2	V
Body Diode Reverse Recovery Time	t _{rr}	I _F = - 10 A, dI/dt = 100 A/μs, T _J = 25 °C		18	36	ns
Body Diode Reverse Recovery Charge	Q _{rr}			8	16	nC
Reverse Recovery Fall Time	t _a			7		ns
Reverse Recovery Rise Time	t _b			11		

Notes:

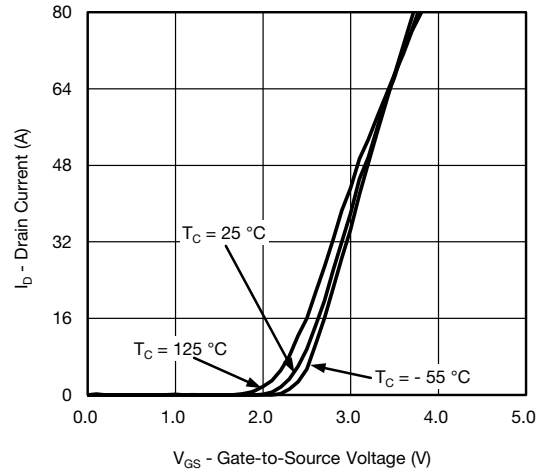
a. Pulse test; pulse width $\leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$.

b. Guaranteed by design, not subject to production testing.

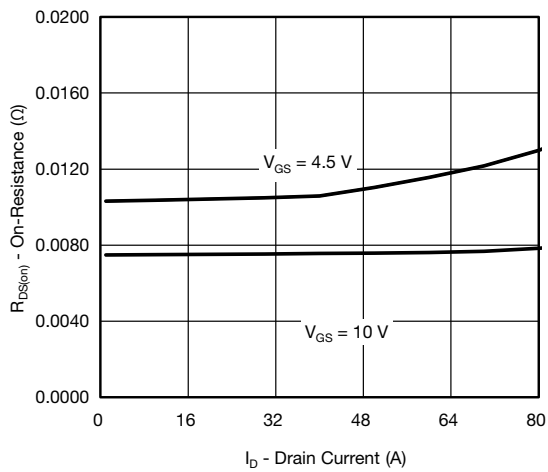
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



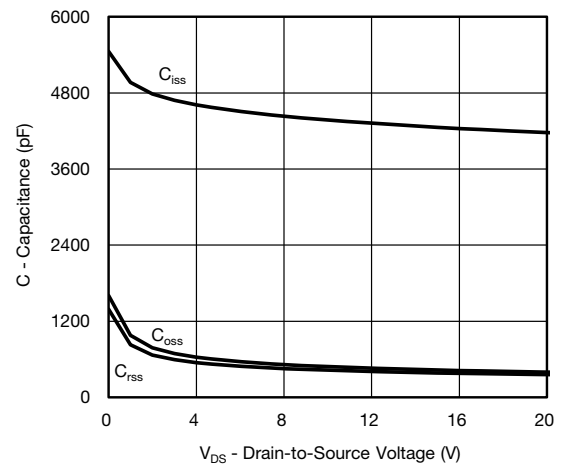
Output Characteristics



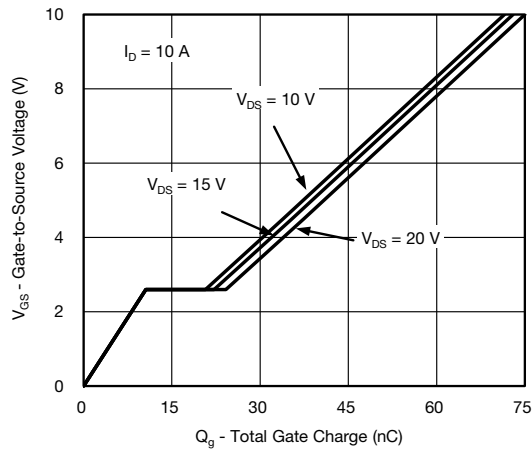
Transfer Characteristics



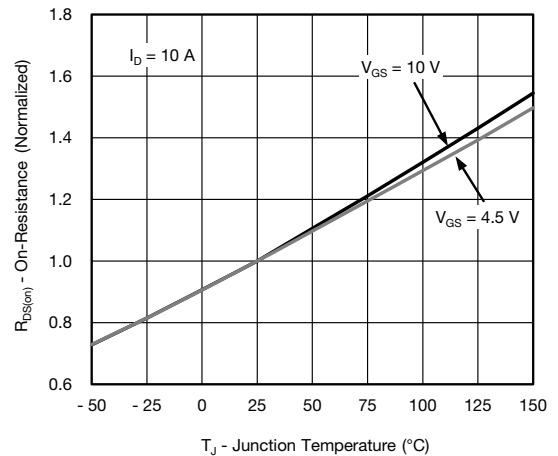
On-Resistance vs. Drain Current



Capacitance

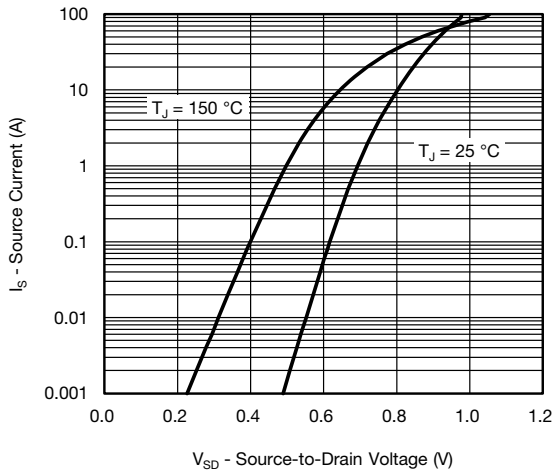


Gate Charge

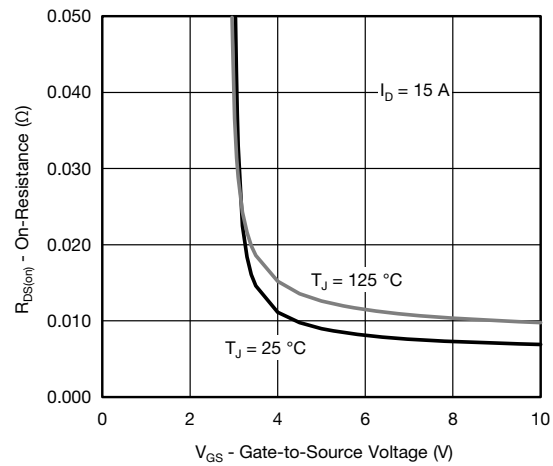


On-Resistance vs. Junction Temperature

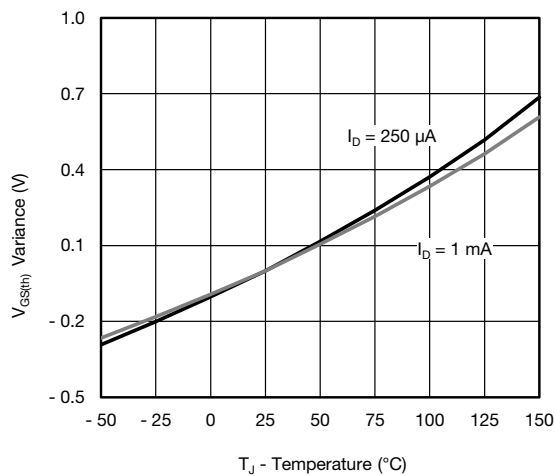
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



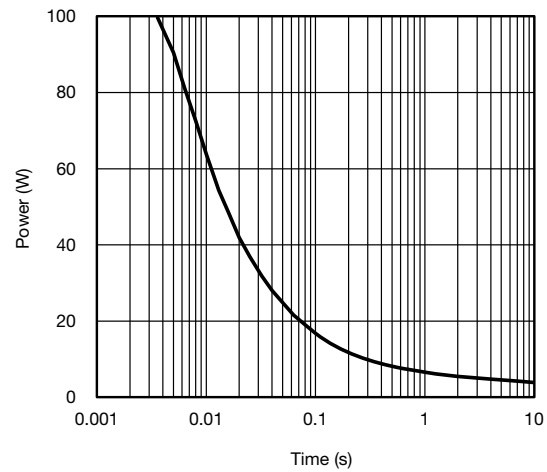
Source-Drain Diode Forward Voltage



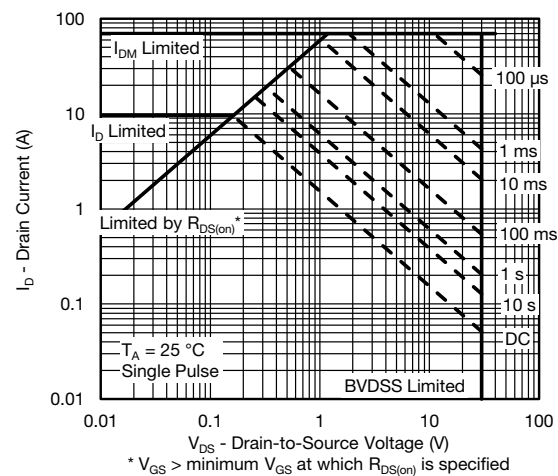
On-Resistance vs. Gate-to-Source Voltage



Threshold Voltage

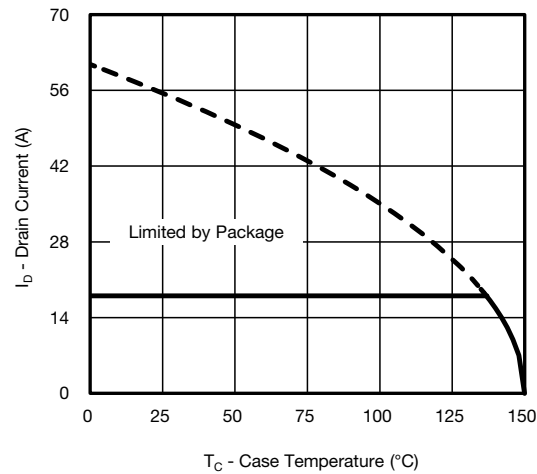
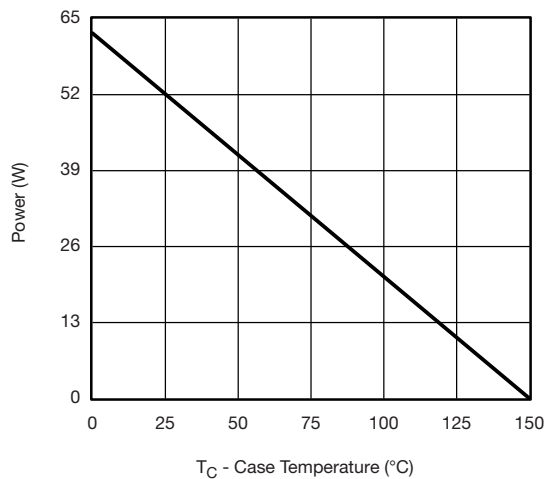
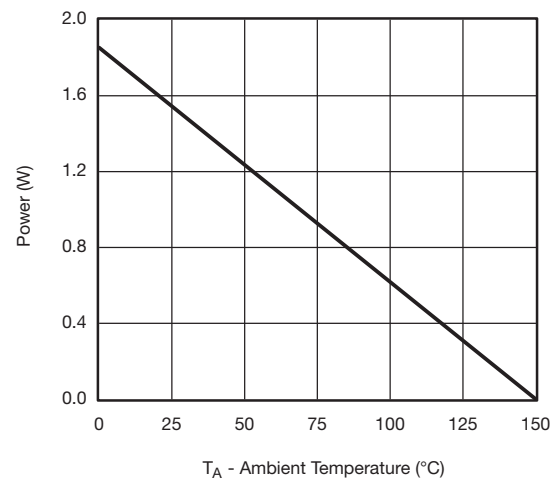


Single Pulse Power, Junction-to-Ambient

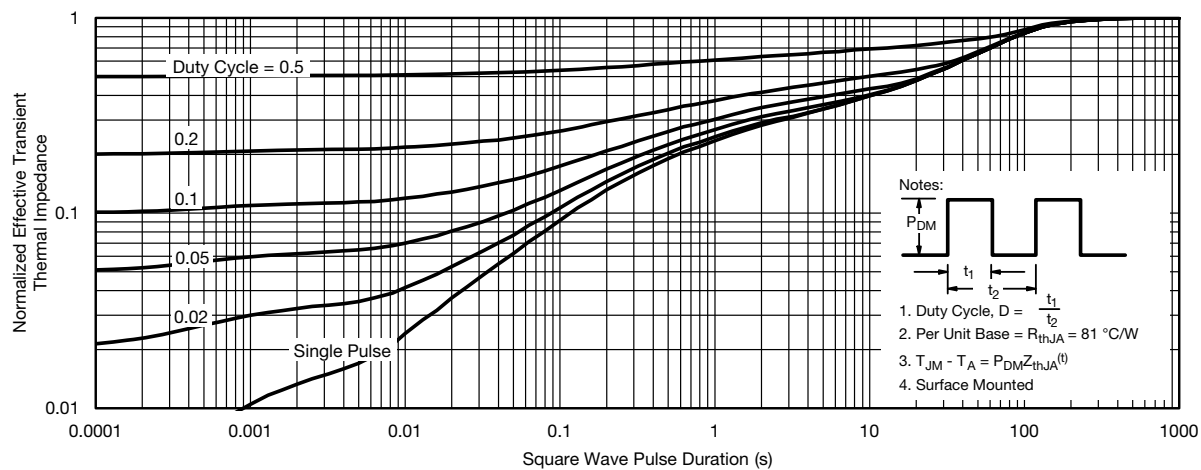
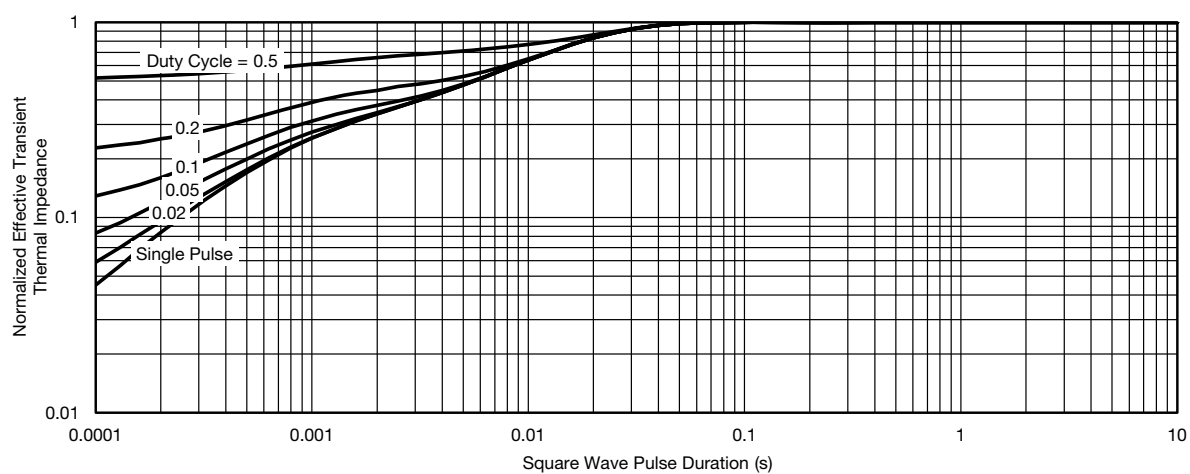


Safe Operating Area

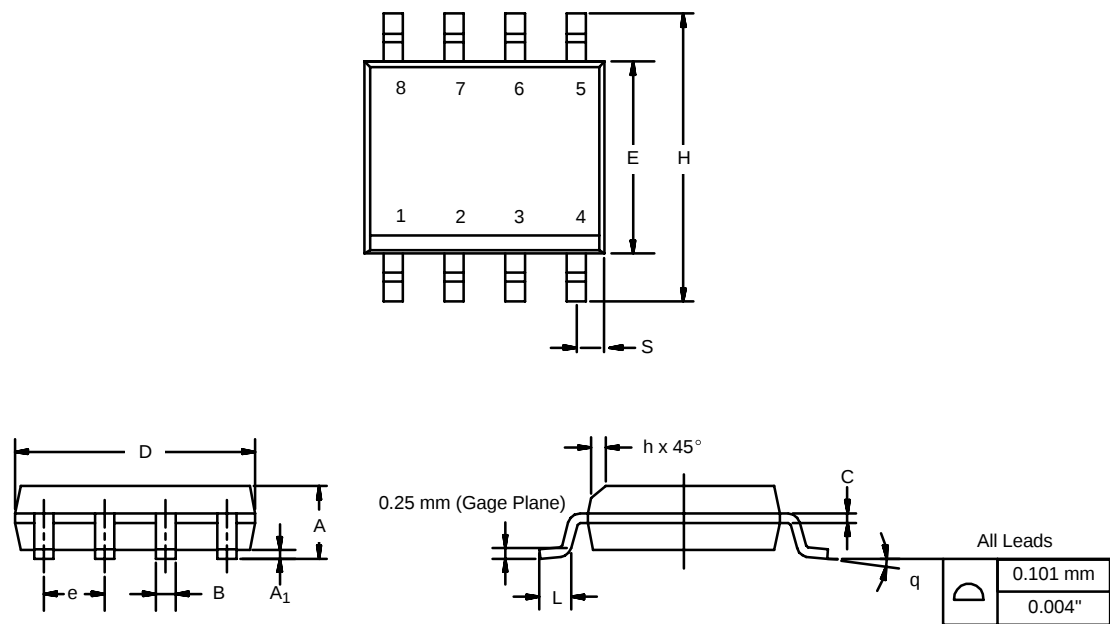
* $V_{GS} >$ minimum V_{GS} at which $R_{DS(on)}$ is specified

MOSFET TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

Current Derating*

Power, Junction-to-Case

Power, Junction-to-Ambient

* The power dissipation P_D is based on $T_{J(max)} = 150$ °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.

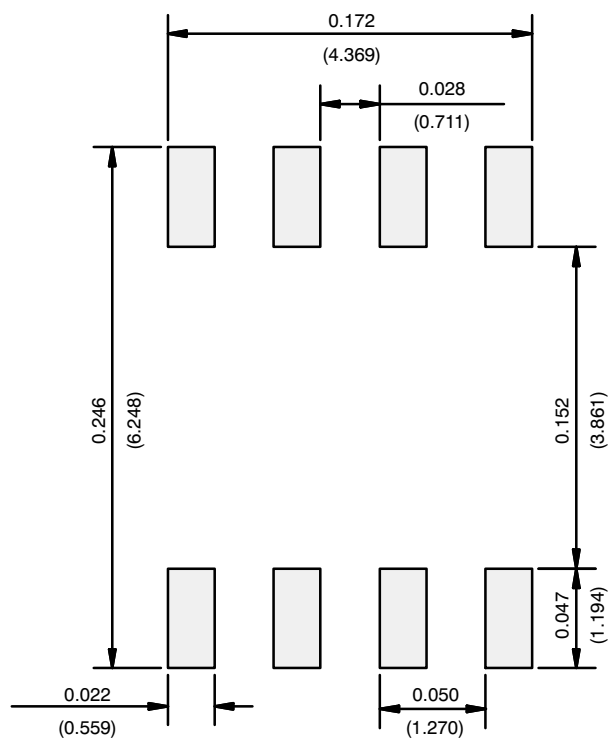
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

Normalized Thermal Transient Impedance, Junction-to-Ambient

Normalized Thermal Transient Impedance, Junction-to-Case

SOIC (NARROW): 8-LEAD
JEDEC Part Number: MS-012



DIM	MILLIMETERS		INCHES	
	Min	Max	Min	Max
A	1.35	1.75	0.053	0.069
A ₁	0.10	0.20	0.004	0.008
B	0.35	0.51	0.014	0.020
C	0.19	0.25	0.0075	0.010
D	4.80	5.00	0.189	0.196
E	3.80	4.00	0.150	0.157
e	1.27 BSC		0.050 BSC	
H	5.80	6.20	0.228	0.244
h	0.25	0.50	0.010	0.020
L	0.50	0.93	0.020	0.037
q	0°	8°	0°	8°
S	0.44	0.64	0.018	0.026
ECN: C-06527-Rev. I, 11-Sep-06				
DWG: 5498				

RECOMMENDED MINIMUM PADS FOR SO-8



Recommended Minimum Pads
Dimensions in Inches/(mm)

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